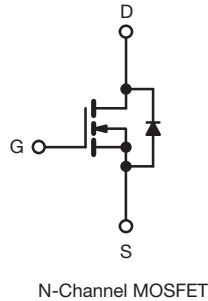


E Series Power MOSFET

Thin-Lead TO-220 FULLPAK



FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Renewable energy
 - Solar (PV inverters)

| PRODUCT SUMMARY | |
|---|-----------------------|
| V_{DS} (V) at T_J max. | 700 |
| $R_{DS(on)}$ max. (Ω) at 25 °C | $V_{GS} = 10$ V 0.6 |
| Q_g max. (nC) | 48 |
| Q_{gs} (nC) | 6 |
| Q_{gd} (nC) | 11 |
| Configuration | Single |

| ORDERING INFORMATION | |
|---------------------------------|--------------------------|
| Package | Thin-Lead TO-220 FULLPAK |
| Lead (Pb)-free | SiHA6N65E-E3 |
| Lead (Pb)-free and halogen-free | SiHA6N65E-GE3 |


| ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted) | | | | |
|---|------------------|----------------|-------------|------|
| PARAMETER | SYMBOL | | LIMIT | UNIT |
| Drain-source voltage | V_{DS} | | 650 | V |
| Gate-source voltage | V_{GS} | | ± 30 | |
| Continuous drain current ($T_J = 150$ °C) ^e | V_{GS} at 10 V | $T_C = 25$ °C | 7 | A |
| | | $T_C = 100$ °C | 5 | |
| Pulsed drain current ^a | I_{DM} | | 18 | |
| Linear derating factor | | | 0.63 | W/°C |
| Single pulse avalanche energy ^b | E_{AS} | | 56 | mJ |
| Maximum power dissipation | P_D | | 31 | W |
| Operating junction and storage temperature range | T_J, T_{stg} | | -55 to +150 | °C |
| Drain-source voltage slope | $T_J = 125$ °C | | 37 | V/ns |
| Reverse diode dV/dt ^d | | | 27 | |
| Soldering recommendations (peak temperature) ^c | For 10 s | | 300 | °C |
| Mounting torque | M3 screw | | 0.6 | Nm |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 2$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C
- Limited by maximum junction temperature



| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum junction-to-ambient | R_{thJA} | 43 | 65 | °C/W |
| Maximum junction-to-case (drain) | R_{thJC} | 3.1 | 4.0 | |

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|---|---------------------|---|------|------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 650 | - | - | V |
| V_{DS} temperature coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$ | - | 0.73 | - | V/°C |
| Gate-source threshold voltage (N) | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2 | - | 4 | V |
| Gate-source leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | - | - | ± 100 | nA |
| | | $V_{GS} = \pm 30\text{ V}$ | - | - | ± 1 | μA |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$ | - | - | 1 | μA |
| | | $V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | - | - | 10 | |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 3\text{ A}$ | - | 0.5 | 0.6 | Ω |
| Forward transconductance | g_{fs} | $V_{DS} = 30\text{ V}, I_D = 3\text{ A}$ | - | 2 | - | S |
| Dynamic | | | | | | |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$ | 410 | 820 | 1640 | pF |
| Output capacitance | C_{oss} | | 20 | 40 | 80 | |
| Reverse transfer capacitance | C_{rss} | | 2 | 4 | 8 | |
| Effective output capacitance, energy related ^a | $C_{o(er)}$ | $V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$ | - | 36 | - | |
| Effective output capacitance, time related ^b | $C_{o(tr)}$ | | - | 117 | - | |
| Total gate charge | Q_g | $V_{GS} = 10\text{ V}, I_D = 3\text{ A}, V_{DS} = 520\text{ V}$ | - | 24 | 48 | nC |
| Gate-source charge | Q_{gs} | | - | 6 | - | |
| Gate-drain charge | Q_{gd} | | - | 11 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 520\text{ V}, I_D = 3\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$ | - | 14 | 28 | ns |
| Rise time | t_r | | - | 12 | 24 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 30 | 60 | |
| Fall time | t_f | | - | 20 | 40 | |
| Gate input resistance | R_g | $f = 1\text{ MHz}, \text{open drain}$ | 0.4 | 1.4 | 2.7 | Ω |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous source-drain diode current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 7 | A |
| Pulsed diode forward current | I_{SM} | | - | - | 18 | |
| Diode forward voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = 3\text{ A}, V_{GS} = 0\text{ V}$ | - | 0.83 | 1.3 | V |
| Reverse recovery time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$ | 118 | 237 | 474 | ns |
| Reverse recovery charge | Q_{rr} | | - | 2.2 | - | μC |
| Reverse recovery current | I_{RRM} | | - | 16 | - | A |

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
- b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

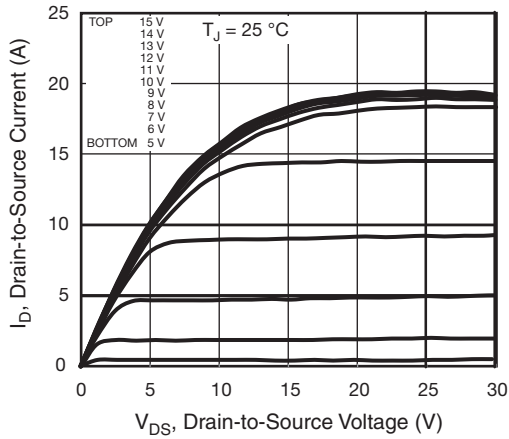


Fig. 1 - Typical Output Characteristics

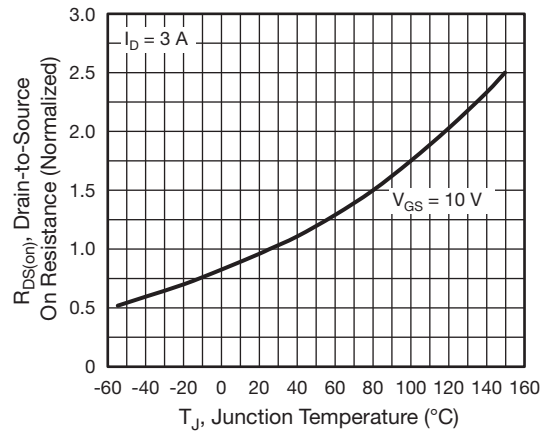


Fig. 4 - Normalized On-Resistance vs. Temperature

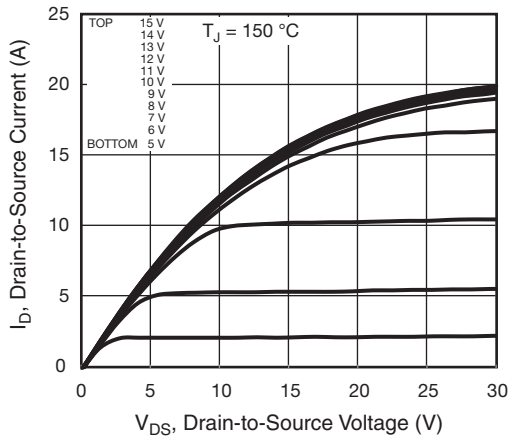


Fig. 2 - Typical Output Characteristics

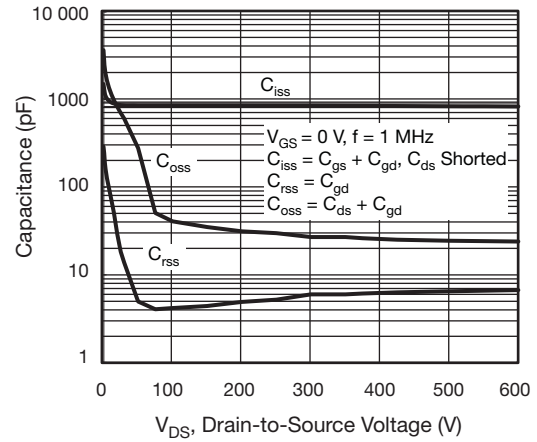


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

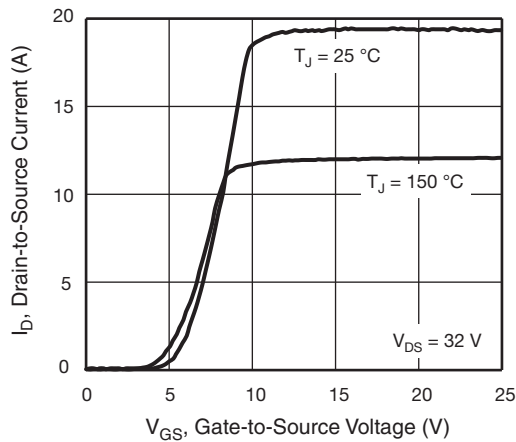


Fig. 3 - Typical Transfer Characteristics

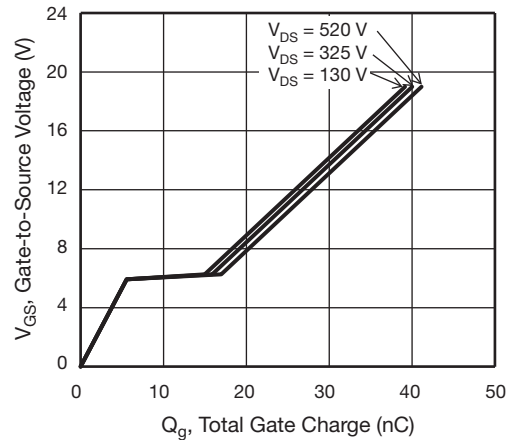


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

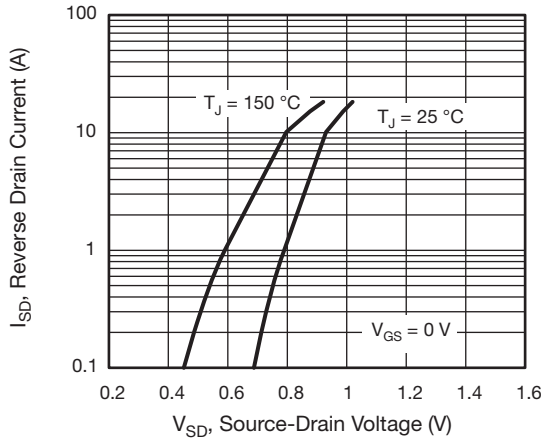


Fig. 7 - Typical Source-Drain Diode Forward Voltage

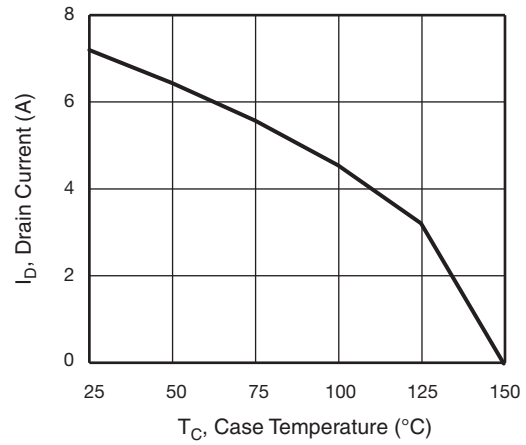


Fig. 9 - Maximum Drain Current vs. Case Temperature

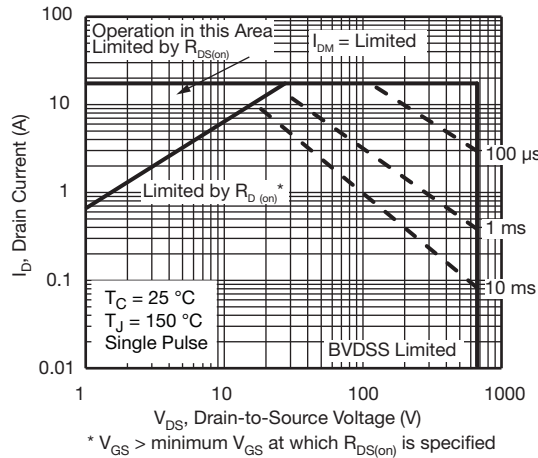


Fig. 8 - Maximum Safe Operating Area

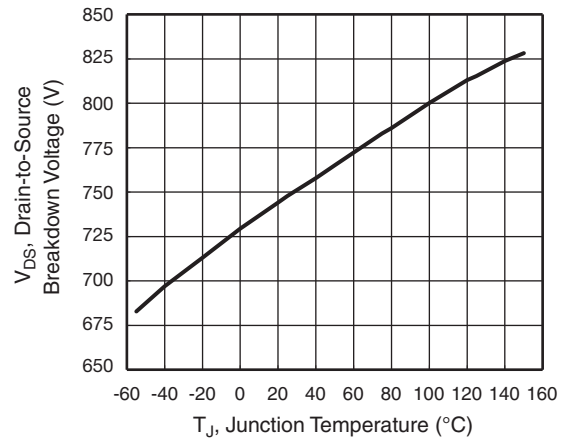


Fig. 10 - Temperature vs. Drain-to-Source Voltage

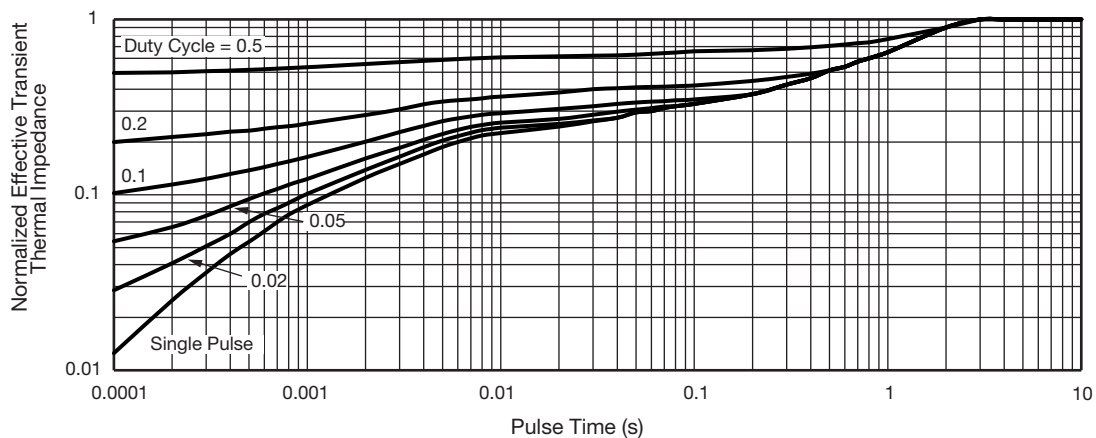


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

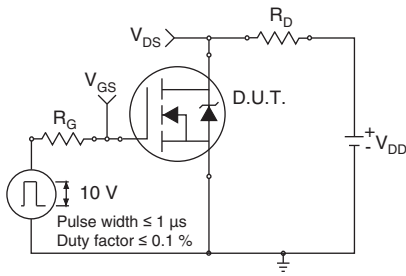


Fig. 12 - Switching Time Test Circuit

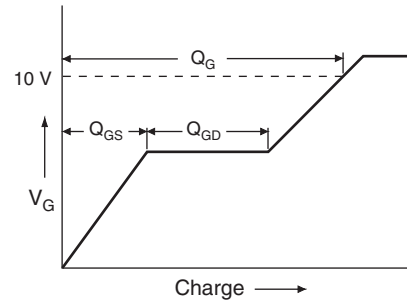


Fig. 16 - Basic Gate Charge Waveform

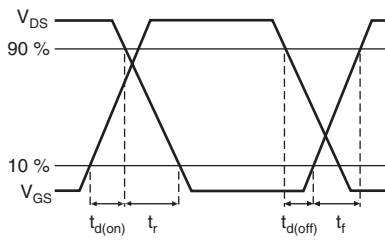


Fig. 13 - Switching Time Waveforms

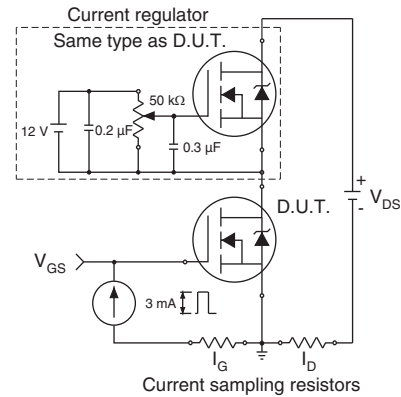


Fig. 17 - Gate Charge Test Circuit

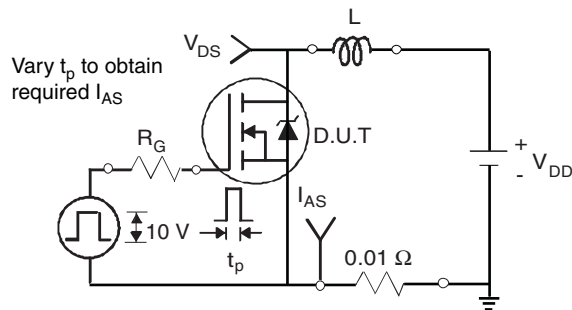


Fig. 14 - Unclamped Inductive Test Circuit

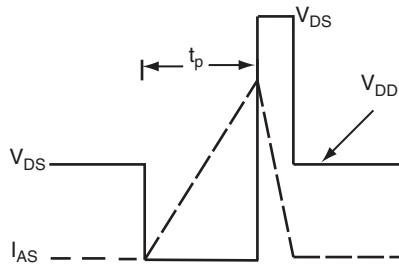
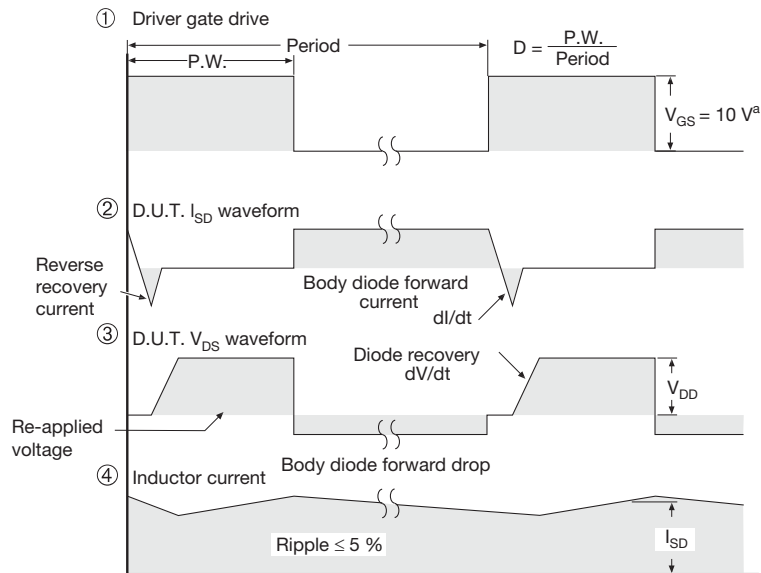
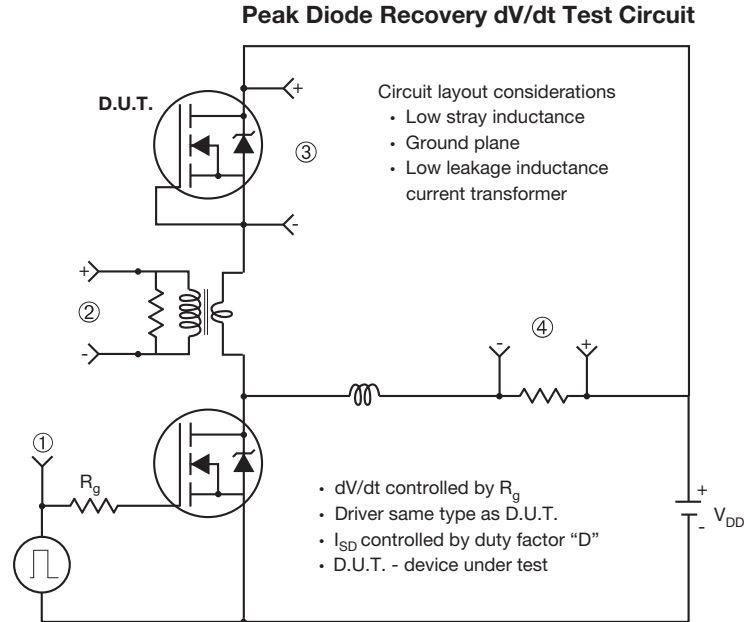


Fig. 15 - Unclamped Inductive Waveforms



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 18 - For N-Channel

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TO-220 FULLPAK Thin Lead



| SYMBOL | DIMENSIONS | | | |
|-----------------|-------------|-------|--------|-------|
| | MILLIMETERS | | INCHES | |
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.30 | 4.70 | 0.169 | 0.185 |
| A1 | 2.50 | 2.90 | 0.098 | 0.114 |
| A2 | 2.40 | 2.80 | 0.094 | 0.110 |
| b | 0.60 | 0.80 | 0.024 | 0.031 |
| b2 | 0.60 | 0.90 | 0.024 | 0.035 |
| c | - | 0.60 | - | 0.024 |
| D | 8.30 | 8.70 | 0.327 | 0.342 |
| d1 | 14.70 | 15.30 | 0.579 | 0.602 |
| d2 | 2.90 | 3.10 | 0.114 | 0.122 |
| d3 | 3.30 | 3.70 | 0.130 | 0.146 |
| E | 9.70 | 10.30 | 0.382 | 0.406 |
| e | 2.50 | 2.70 | 0.098 | 0.106 |
| L | 13.40 | 13.80 | 0.528 | 0.543 |
| L1 | 1.00 | 2.80 | 0.039 | 0.110 |
| $\varnothing P$ | 3.00 | 3.40 | 0.118 | 0.134 |

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DWG: 6021



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